



Thyristor

$V_{RRM} = 1400\text{ V}$

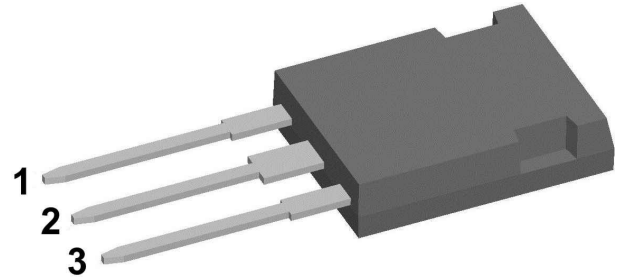
$I_{TAV} = 60\text{ A}$

$V_T = 1.14\text{ V}$

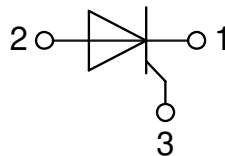
Single Thyristor

Part number

CS60-14io1



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: PLUS247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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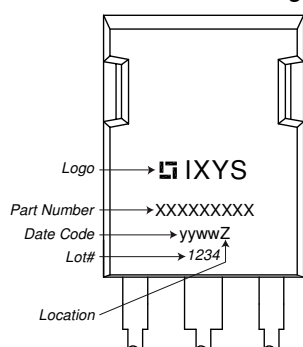


Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1500	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1400	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1400\text{ V}$	$T_{VJ} = 25^{\circ}C$		200	μA
		$V_{R/D} = 1400\text{ V}$	$T_{VJ} = 140^{\circ}C$		10	mA
V_T	forward voltage drop	$I_T = 60\text{ A}$	$T_{VJ} = 25^{\circ}C$		1.18	V
		$I_T = 120\text{ A}$			1.44	V
		$I_T = 60\text{ A}$	$T_{VJ} = 125^{\circ}C$		1.14	V
		$I_T = 120\text{ A}$			1.46	V
I_{TAV}	average forward current	$T_C = 110^{\circ}C$	$T_{VJ} = 140^{\circ}C$		60	A
$I_{T(RMS)}$	RMS forward current	180° sine			75	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0.82	V
r_T	slope resistance				5.3	m Ω
R_{thJC}	thermal resistance junction to case				0.32	K/W
R_{thCH}	thermal resistance case to heatsink			0.15		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		360	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		1.40	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		1.51	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		1.19	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		1.29	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		9.80	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		9.49	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		7.08	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		6.87	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V } f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		74	pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu s$	$T_C = 140^{\circ}C$		10	W
		$t_p = 300\text{ }\mu s$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50\text{ Hz}$ repetitive, $I_T = 180\text{ A}$			150	A/ μs
		$t_p = 200\text{ }\mu s; di_G/dt = 0.3\text{ A}/\mu s;$ $I_G = 0.3\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 60\text{ A}$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 140^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		1.5	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		100	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10\text{ }\mu s$	$T_{VJ} = 25^{\circ}C$		450	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu s$				
I_H	holding current	$V_D = 6\text{ V } R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu s$				
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 60\text{ A}; V = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu s \quad dv/dt = 20\text{ V}/\mu s \quad t_p = 200\text{ }\mu s$	$T_{VJ} = 125^{\circ}C$		150	μs



Package PLUS247		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		140	°C
Weight				6		g
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	5.5			mm
$d_{Spb/Apb}$		terminal to backside	5.5			mm

Product Marking



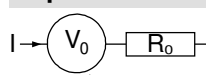
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CS60-14io1	CS60-14io1	Tube	30	507901

Similar Part	Package	Voltage class
CS60-12io1	PLUS247 (3)	1200
CS60-16io1	PLUS247 (3)	1600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}C$

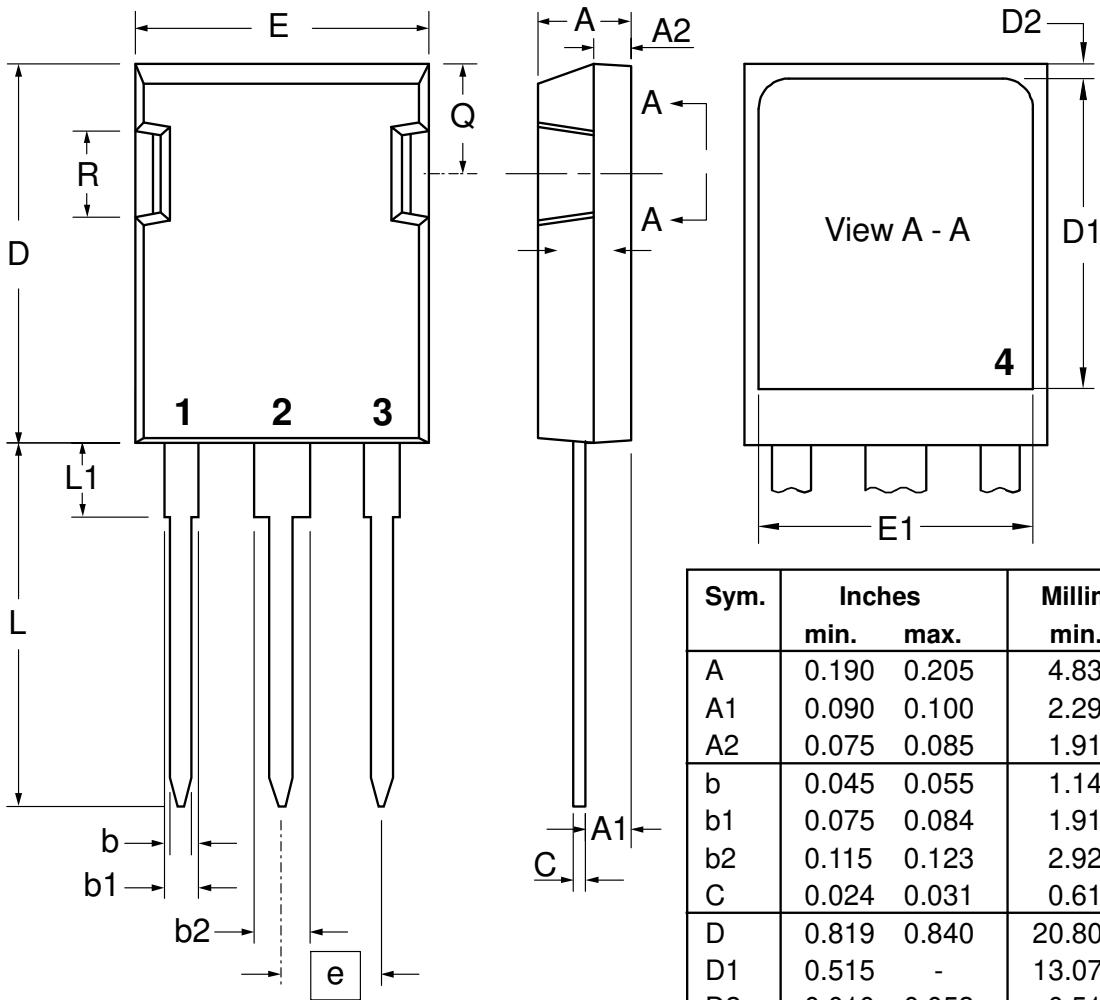


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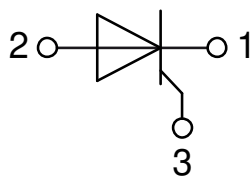
$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	3	mΩ



Outlines PLUS247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.190	0.205	4.83	5.21
A1	0.090	0.100	2.29	2.54
A2	0.075	0.085	1.91	2.16
b	0.045	0.055	1.14	1.40
b1	0.075	0.084	1.91	2.13
b2	0.115	0.123	2.92	3.12
C	0.024	0.031	0.61	0.80
D	0.819	0.840	20.80	21.34
D1	0.515	-	13.07	-
D2	0.010	0.053	0.51	1.35
E	0.620	0.635	15.75	16.13
E1	0.530	-	13.45	-
e	0.215 BSC		5.45 BSC	
L	0.780	0.800	19.81	20.32
L1	0.150	0.170	3.81	4.32
Q	0.220	0.244	5.59	6.20
R	0.170	0.190	4.32	4.83



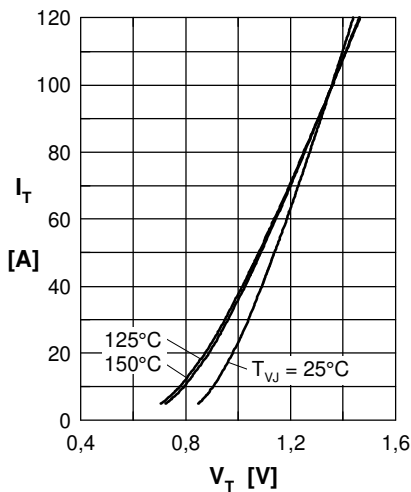
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Fig. 1 Forward characteristics

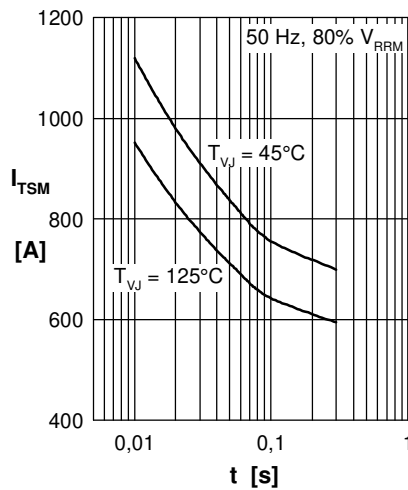


Fig. 2 Surge overload current

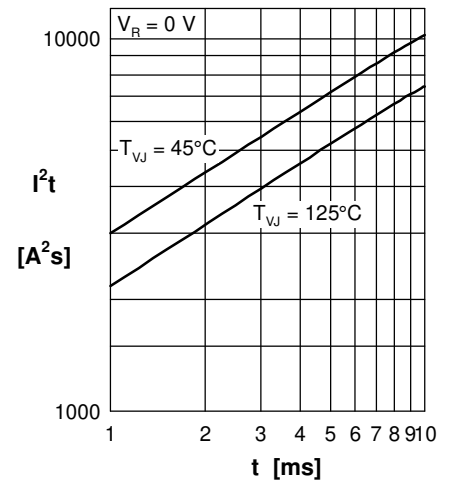
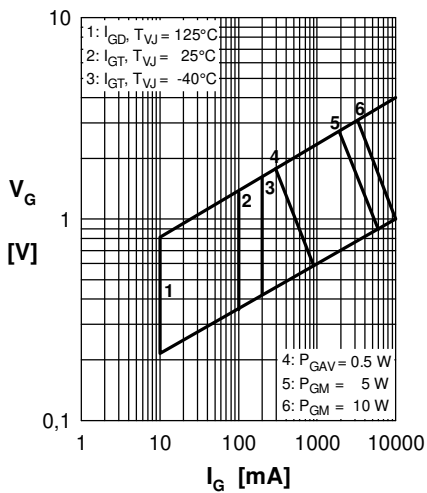

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics

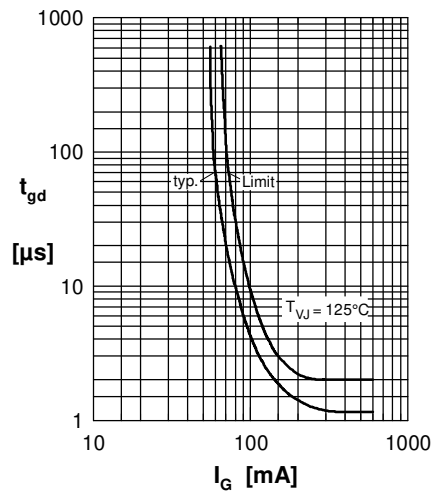


Fig. 5 Gate controlled delay time

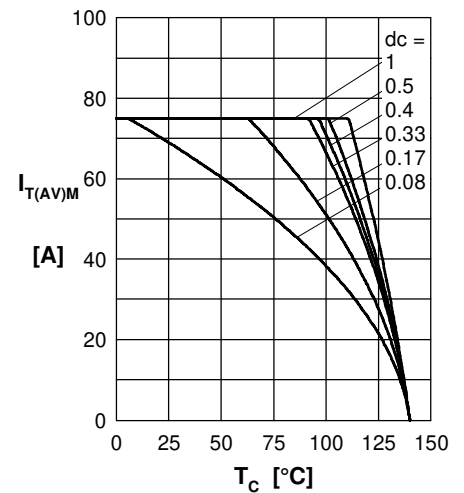


Fig. 6 Max. forward current at case temperature

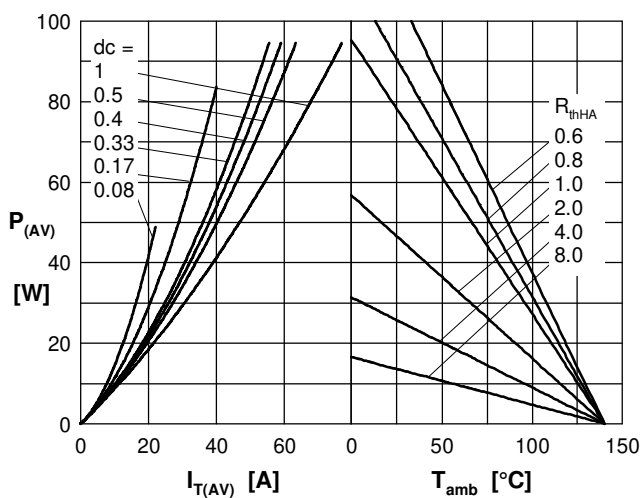
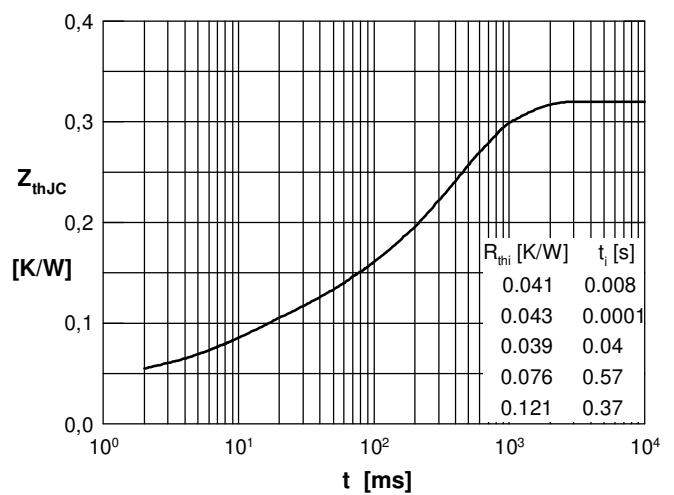

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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